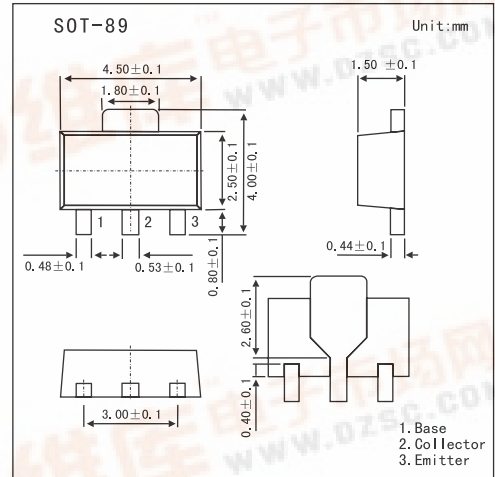


SMD Type Transistors

NPN Silicon Epitaxia
2SC3618

■ Features

- World standard miniature package.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|----------------------------|------------------|-------------|------|
| Collector-base voltage | V _{CB0} | 25 | V |
| Collector-emitter voltage | V _{CEO} | 25 | V |
| Emitter-base voltage | V _{EB0} | 15 | V |
| Collector current | I _C | 0.7 | A |
| Collector current (Pulse)* | I _{CP} | 1.0 | A |
| Total power dissipation | P _T | 2.0 | W |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

* PW ≤ 10ms, duty cycle ≤ 50%.

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|--|----------------------|---|-----|------|------|------|
| Collector cutoff current | I _{CBO} | V _{CB} = 25V, I _E = 0 | | | 100 | nA |
| Emitter cutoff current | I _{EBO} | V _{EB} = 10V, I _C = 0 | | | 100 | nA |
| DC current gain * | h _{FE} | V _{CE} = 2.0V, I _C = 300mA | 800 | | 3200 | |
| Collector-emitter saturation voltage * | V _{CE(sat)} | I _C = 300mA, I _B = 3.0mA | | 0.16 | 0.3 | V |
| Base-emitter saturation voltage * | V _{BE(sat)} | I _C = 300mA, I _B = 3.0mA | | 0.75 | 1.2 | V |
| Gain bandwidth product | f _T | V _{CE} = 5.0V, I _E = -300mA | 150 | 250 | | MHz |
| Output capacitance | C _{ob} | V _{CB} = 10V, I _E = 0, f = 1.0MHz | | 10 | | pF |

*. PW ≤ 350μs, duty cycle ≤ 2%

■ hFE Classification

| Marking | UM | UL | UK |
|---------|----------|-----------|-----------|
| hFE | 800~1600 | 1200~2400 | 2000~3200 |

